

REMARKS

The title has been amended to conform to the elected claims. Independent Claims 1 and 10 have been canceled and new Claims 20 and 21 have been substituted therefore. Claim 20, unlike original Claim 1, now refers to the substrate, as in the specification. Moreover, the term "dielectric" has been substituted for the term "high k." It is respectfully submitted that in the field the term "high k" inherently means dielectric. Hence the term "dielectric" is supported. Also, rather than "channel", Claim 20 now refers to "channel region" which is believed to make the claim clearer. Also, rather than referring to a "gate," the term "gate electrode" has been substituted. It is respectfully submitted that it is well known in the field that it is inherent that a gate have a gate electrode.

Hence these claim amendments are merely to improve the form of the claims and do not narrow same and are not intended to distinguish over any references.

Amendments to the dependent claims are to conform to the independent claims and to clarify same.

New Claim 21, which substitutes for Claim 10, contains language similar to that of Claim 20.

If there are any questions regarding this Amendment, please telephone the undersigned at (408) 453-9200.

EXPRESS MAIL LABEL NO:

EL 937 078 657 US

Respectfully submitted,



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APPENDIX A - Version to show changes to the claims

2. (Amended) The device of Claim 20 [1] wherein each of the dielectric [high k] layer, the buffer layer, and the blocking layer comprise epitaxial layers.
3. (Amended) The device of Claim 20 [1] wherein the gate electrode comprises silicon germanium.
4. (Amended) The device of Claim 20 [1] wherein each of the buffer layer and the blocking layer comprise silicon.
5. (Amended) The device of Claim 20 [1] wherein each of the source/drain regions comprises silicon germanium.
7. (Amended) The device of Claim 20 [1] wherein the dielectric [high k] layer is selected from the group consisting of oxides of zircon, oxides of titanium, oxides of tantalum, and oxides of hafnium.
8. (Amended) The device of Claim 20 [1] wherein the blocking layer comprises less than or equal to ten layers of atomic silicon in thickness.
9. (Amended) The device of Claim 20 [1] wherein the buffer layer comprises less than or equal to ten layers of atomic silicon in thickness.
11. (Amended) The device of Claim 21 [10] wherein the gate electrode comprises a metal.
12. (Amended) The device of Claim 21 [10] wherein each of the source/drain regions has a depth into the well of about 100 to about 1000 Angstroms [angstroms].
13. (Amended) The device of Claim 21 [10] wherein the source/drain regions comprise amorphous material.